

### General Description

**SRFET™** The AO4722 uses advanced trench technology with a monolithically integrated Schottky diode to provide excellent  $R_{DS(ON)}$ , and low gate charge. This device is suitable for use as a low side FET in SMPS, load switching and general purpose applications.

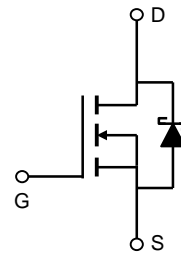
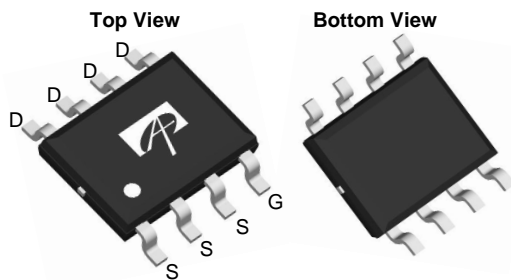
### Product Summary

$V_{DS}$  (V) = 30V  
 $I_D = 11.6A$  ( $V_{GS} = 10V$ )  
 $R_{DS(ON)} < 14m\Omega$  ( $V_{GS} = 10V$ )  
 $R_{DS(ON)} < 22m\Omega$  ( $V_{GS} = 4.5V$ )

100% UIS Tested  
 100% Rg Tested



SOIC-8



**SRFET™**  
 Soft Recovery MOSFET:  
 Integrated Schottky Diode

### Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	10 Sec	Steady State	Units	
Drain-Source Voltage	$V_{DS}$	30		V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$			
Continuous Drain Current <sup>A</sup>	$I_{DSM}$	$T_A=25^\circ C$	11.6	8.5	A
		$T_A=70^\circ C$	9.3	6.8	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	100			
Avalanche Current <sup>B</sup>	$I_{AR}$	17			
Repetitive avalanche energy $L=0.3mH$ <sup>B</sup>	$E_{AR}$	43		mJ	
Power Dissipation	$P_{DSM}$	$T_A=25^\circ C$	3.1	1.7	W
		$T_A=70^\circ C$	2.0	1.1	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150		$^\circ C$	

### Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	32	40	$^\circ C/W$
Maximum Junction-to-Ambient <sup>A</sup>		60	75	$^\circ C/W$
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	17	24	$^\circ C/W$

Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$ , $V_{GS}=0\text{V}$	30			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=30\text{V}$ , $V_{GS}=0\text{V}$ $T_J=125^\circ\text{C}$			0.1 10	mA
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 20\text{V}$			0.1	$\mu\text{A}$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	1.3	1.65	2.5	V
$I_{D(ON)}$	On state drain current	$V_{GS}=10\text{V}$ , $V_{DS}=5\text{V}$	100			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$ , $I_D=11.6\text{A}$ $T_J=125^\circ\text{C}$		11.5	14	m $\Omega$
		$V_{GS}=4.5\text{V}$ , $I_D=9.3\text{A}$		17	21	
$g_{FS}$	Forward Transconductance	$V_{DS}=5\text{V}$ , $I_D=11.6\text{A}$		28		S
$V_{SD}$	Diode Forward Voltage	$I_S=1\text{A}$ , $V_{GS}=0\text{V}$		0.43	0.5	V
$I_S$	Maximum Body-Diode + Schottky Continuous Current				4	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}$ , $V_{DS}=15\text{V}$ , $f=1\text{MHz}$		903	1100	pF
$C_{oss}$	Output Capacitance			225		pF
$C_{rss}$	Reverse Transfer Capacitance			91		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}$ , $V_{DS}=0\text{V}$ , $f=1\text{MHz}$		1.7	2.6	$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$ , $V_{DS}=15\text{V}$ , $I_D=11.6\text{A}$		15.3	20	nC
$Q_g(4.5\text{V})$	Total Gate Charge			7.8	10	nC
$Q_{gs}$	Gate Source Charge			2.0		nC
$Q_{gd}$	Gate Drain Charge			3.9		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$ , $V_{DS}=15\text{V}$ , $R_L=1.3\Omega$ , $R_{GEN}=3\Omega$		5.0		ns
$t_r$	Turn-On Rise Time			9.2		ns
$t_{D(off)}$	Turn-Off DelayTime			17.8		ns
$t_f$	Turn-Off Fall Time			4.4		ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=11.6\text{A}$ , $dI/dt=300\text{A}/\mu\text{s}$		17	20	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=11.6\text{A}$ , $dI/dt=300\text{A}/\mu\text{s}$		30.0		nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using  $<300\mu\text{s}$  pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

F: The current rating is based on the  $t \leq 10\text{s}$  junction to ambient thermal resistance rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

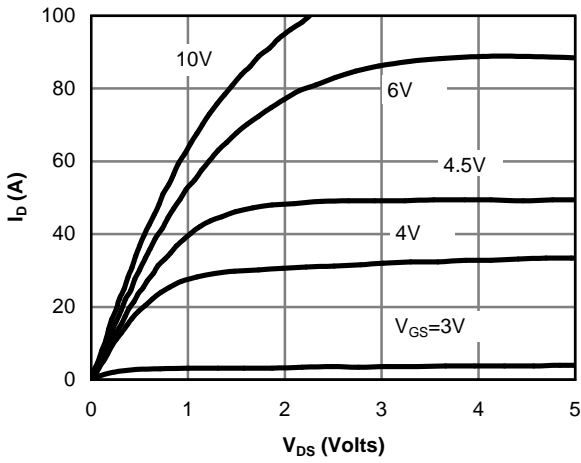


Figure 1: On-Region Characteristics

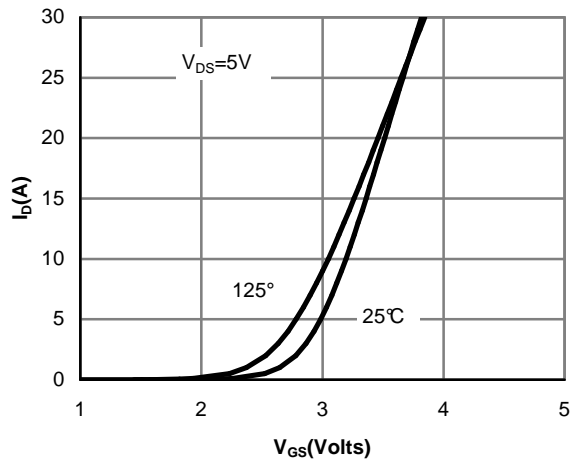


Figure 2: Transfer Characteristics

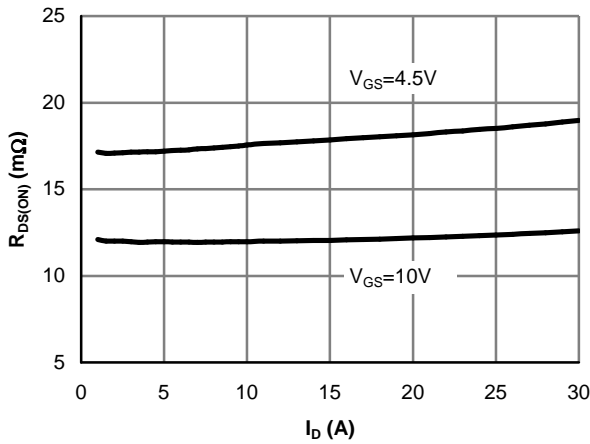


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

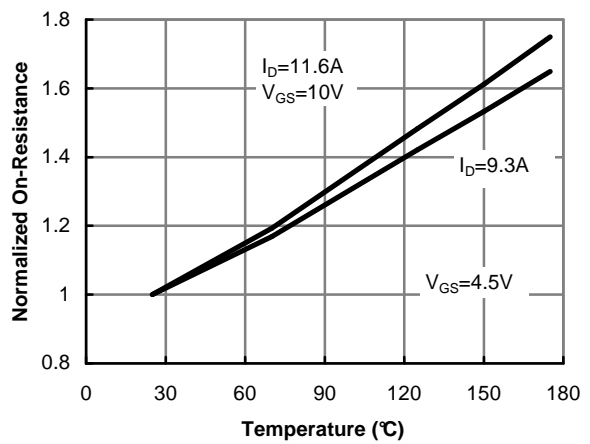


Figure 4: On-Resistance vs. Junction Temperature

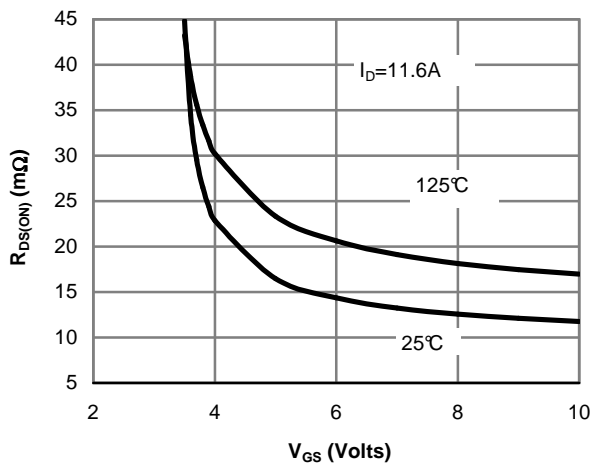


Figure 5: On-Resistance vs. Gate-Source Voltage

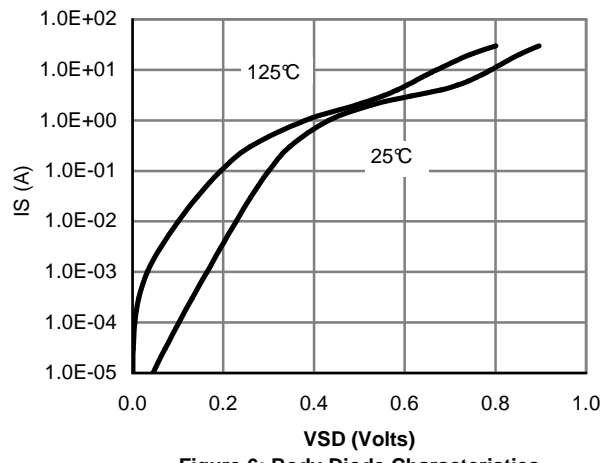


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

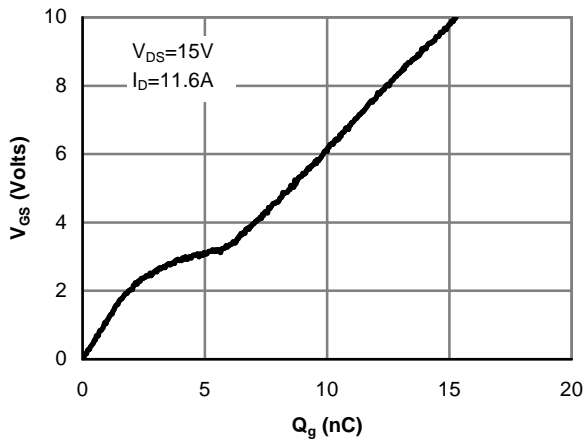


Figure 7: Gate-Charge Characteristics

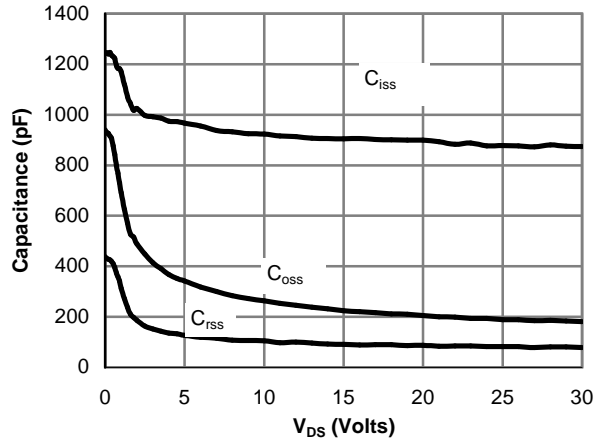


Figure 8: Capacitance Characteristics

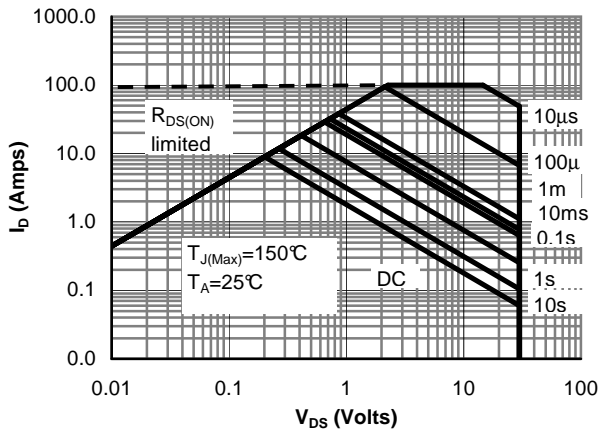


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

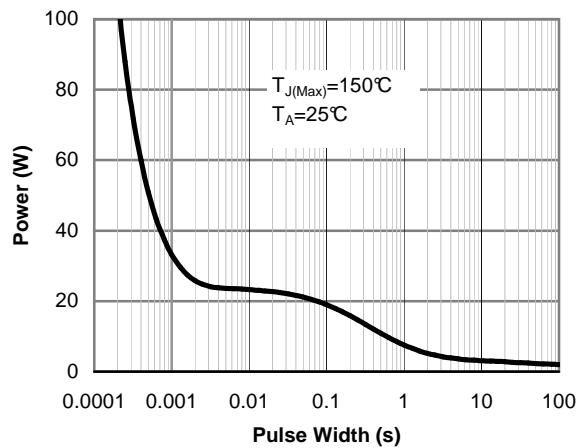


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

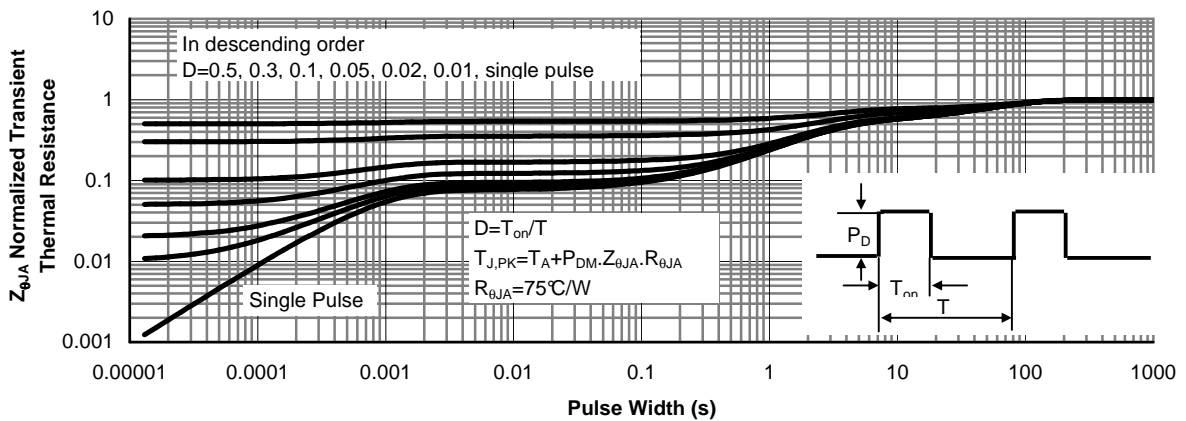


Figure 11: Normalized Maximum Transient Thermal Impedance (Note E)

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